

II. AMENDMENTS TO THE CLAIMS:

1 – 8. (Cancelled)

9. (Currently Amended) A method of forming a vertical bipolar transistor having a single crystal base formed on a substrate, the method comprising the steps of:

- a) forming a silicon dioxide layer and a dielectric layer on the single crystal base;
- b) forming an emitter window in the dielectric layer over the single crystal base to expose a portion of the silicon dioxide layer;
- c) reacting the portion of the silicon dioxide layer to form a reaction product layer;
- d) removing the reaction product layer from the emitter window to expose a surface of a portion of the single crystal base;
- e) annealing the substrate in an inert atmosphere; and
- f) forming a single crystal emitter on the exposed surface of the single crystal base.

10. (Original) The method of claim 9, wherein the step (e) comprises annealing in a reducing atmosphere.

11. (Original) The method of claim 10, wherein the reducing atmosphere comprises hydrogen.

12. (Original) The method of claim 9, wherein steps (d)-(f) are performed in an oxygen-free ambient to prevent formation of a native oxide layer.

13. (Original) The method of claim 9, wherein steps (d)-(f) are performed in the same process chamber.
14. (Original) The method of claim 9, wherein the annealing step (e) comprises a temperature from approximately 700°C to approximately 800°C.
15. (Currently Amended) The method of claim 9, wherein the single crystal base includes germanium.
16. (Original) The method of claim 9, wherein the dielectric layer comprises silicon nitride.
17. (Original) The method of claim 9, wherein the reacting step (c) comprises a vapor phase etch.
18. (Original) The method of claim 9, wherein the removing step includes evaporating the reaction product from the surface.

19. (Original) A method of forming an interface between a first single crystal silicon layer and a second single crystal silicon layer, the method comprising the steps of:

- a) forming a silicon dioxide layer on the second single crystal silicon layer;
- b) reacting at least a portion of the silicon dioxide layer to form a reaction product layer;
- c) removing the reaction product layer to expose a surface of the second single crystal silicon layer;
- d) annealing in an inert atmosphere; and
- e) forming the first single crystal silicon layer on the surface of the second single crystal silicon layer.

20. (Original) The method of claim 19, wherein the inert atmosphere comprises hydrogen.